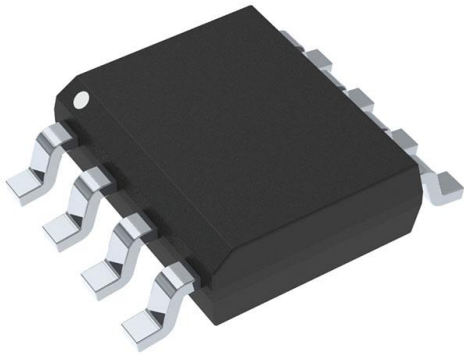


# NTMSD6N303R2 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	NTMSD6N303R2-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	NTMSD6N303R2
Description	MOSFET N-CH 30V 6A 8SOIC
Detailed Description	N-Channel 30 V 6A (Ta) 2W (Ta) Surface Mount 8-SO IC



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

NTMSD6N303R2

Series:

FETKY™

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.5V @ 250µA

Vgs (Max):

±20V

FET Feature:

Schottky Diode (Isolated)

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

8-SOIC

Base Product Number:

NTMSD6

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

6A (Ta)

Rds On (Max) @ Id, Vgs:

32mOhm @ 6A, 10V

Gate Charge (Qg) (Max) @ Vgs:

30 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

950 pF @ 24 V

Power Dissipation (Max):

2W (Ta)

Mounting Type:

Surface Mount

Package / Case:

8-SOIC (0.154", 3.90mm Width)

## Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



# NTMSD6N303, NVMSD6N303

## Power MOSFET

### 6 Amps, 30 Volts N-Channel SO-8 FETKY™

The FETKY product family incorporates low  $R_{DS(on)}$  MOSFETs packaged with an industry leading, low forward drop, low leakage Schottky Barrier rectifier to offer high efficiency components in a space saving configuration. Independent pinouts for MOSFET and Schottky die allow the flexibility to use a single component for switching and rectification functions in a wide variety of applications.

#### Features

- These Devices are Pb-Free and are RoHS Compliant
- NVMSD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

#### Applications

- Buck Converter
- Buck-Boost
- Synchronous Rectification
- Low Voltage Motor Control
- Battery Packs
- Chargers
- Cell Phones

#### MOSFET MAXIMUM RATINGS

( $T_J = 25^\circ\text{C}$  unless otherwise noted) (Note 1)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	30	Vdc
Drain-to-Gate Voltage ( $R_{GS} = 1.0\text{ M}\Omega$ )	$V_{DGR}$	30	Vdc
Gate-to-Source Voltage - Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current - (Note 2)			
- Continuous @ $T_A = 25^\circ\text{C}$	$I_D$	6.0	Adc
- Single Pulse ( $t_p \leq 10\ \mu\text{s}$ )	$I_{DM}$	30	Apk
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 2)	$P_D$	2.0	Watts
Single Pulse Drain-to-Source Avalanche Energy - Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = 30\text{ Vdc}$ , $V_{GS} = 5.0\text{ Vdc}$ , $V_{DS} = 20\text{ Vdc}$ , $I_L = 9.0\text{ Apk}$ , $L = 10\text{ mH}$ , $R_G = 25\ \Omega$ )	$E_{AS}$	325	mJ

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width  $\leq 250\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
2. Mounted on 2" square FR4 board  
(1 in sq, 2 oz. Cu 0.06" thick single sided), 10 sec. max.

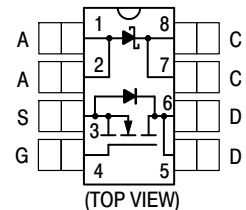


ON Semiconductor®

<http://onsemi.com>

**MOSFET**  
**6.0 AMPERES**  
**30 VOLTS**  
**24 m $\Omega$  @  $V_{GS} = 10\text{ V}$  (Typ)**

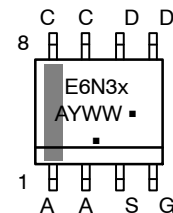
**SCHOTTKY DIODE**  
**6.0 AMPERES**  
**30 VOLTS**  
**420 mV @  $I_F = 3.0\text{ A}$**



#### MARKING DIAGRAM & PIN ASSIGNMENT



SO-8  
CASE 751  
STYLE 18



E6N3 = Device Code  
x = Blank or S  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
NTMSD6N303R2G	SO-8 (Pb-Free)	2500/Tape & Reel
NTMSD6N303R2SG	SO-8 (Pb-Free)	2500/Tape & Reel
NVMSD6N303R2G	SO-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**NTMSD6N303, NVMSD6N303****SCHOTTKY RECTIFIER MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_R$	30	Volts
Average Forward Current (Note 3) (Rated $V_R$ ) $T_A = 104^\circ\text{C}$	$I_O$	2.0	Amps
Peak Repetitive Forward Current (Note 3) (Rated $V_R$ , Square Wave, 20 kHz) $T_A = 108^\circ\text{C}$	$I_{frm}$	4.0	Amps
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half-wave, single phase, 60 Hz)	$I_{fsm}$	30	Amps

**THERMAL CHARACTERISTICS – SCHOTTKY AND MOSFET**

Thermal Resistance – Junction-to-Ambient (Note 4) – MOSFET	$R_{\theta JA}$	167	°C/W
Thermal Resistance – Junction-to-Ambient (Note 5) – MOSFET	$R_{\theta JA}$	97	
Thermal Resistance – Junction-to-Ambient (Note 3) – MOSFET	$R_{\theta JA}$	62.5	
Thermal Resistance – Junction-to-Ambient (Note 4) – Schottky	$R_{\theta JA}$	197	
Thermal Resistance – Junction-to-Ambient (Note 5) – Schottky	$R_{\theta JA}$	97	
Thermal Resistance – Junction-to-Ambient (Note 3) – Schottky	$R_{\theta JA}$	62.5	
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Mounted on 2" square FR4 board (1 in sq, 2 oz. Cu 0.06" thick single sided), 10 sec. max.
- Mounted with minimum recommended pad size, PC Board FR4.
- Mounted on 2" square FR4 board (1 in sq, 2 oz. Cu 0.06" thick single sided), Steady State.

**SCHOTTKY RECTIFIER ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristics	Symbol	Value		Unit
		$T_J = 25^\circ\text{C}$	$T_J = 125^\circ\text{C}$	
Maximum Instantaneous Forward Voltage (Note 6)  $I_F = 100 \text{ mAdc}$ $I_F = 3.0 \text{ Adc}$ $I_F = 6.0 \text{ Adc}$	$V_F$	$T_J = 25^\circ\text{C}$	$T_J = 125^\circ\text{C}$	Volts
		0.28	0.13	
		0.42	0.33	
		0.50	0.45	
Maximum Instantaneous Reverse Current (Note 6)  $V_R = 30 \text{ V}$	$I_R$	$T_J = 25^\circ\text{C}$	$T_J = 125^\circ\text{C}$	$\mu\text{A}$ mA
		250 –	– 25	
Maximum Voltage Rate of Change  $V_R = 30 \text{ V}$	$dV/dt$	10,000		V/ $\mu\text{s}$

- Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**NTMSD6N303, NVMSD6N303****MOSFET ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Drain-to-Source Breakdown Voltage ( $V_{GS} = 0\text{ Vdc}$ , $I_D = 250\ \mu\text{A}$ ) Temperature Coefficient (Positive)	$V_{(BR)DSS}$	30 -	- 30	- -	Vdc mV/°C
Zero Gate Voltage Drain Current ( $V_{DS} = 24\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $T_J = 25^\circ\text{C}$ ) ( $V_{DS} = 24\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $T_J = 125^\circ\text{C}$ )	$I_{DSS}$	- -	- -	1.0 20	$\mu\text{Adc}$
Gate-Body Leakage Current ( $V_{GS} = \pm 20\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	-	-	100	nAdc

**ON CHARACTERISTICS** (Note 7)

Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{Adc}$ ) Temperature Coefficient (Negative)	$V_{GS(th)}$	1.0 -	1.8 4.6	2.5 -	Vdc mV/°C
Static Drain-to-Source On-State Resistance ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 6\text{ Adc}$ ) ( $V_{GS} = 4.5\text{ Vdc}$ , $I_D = 3.9\text{ Adc}$ )	$R_{DS(on)}$	- -	0.024 0.030	0.032 0.040	$\Omega$
Forward Transconductance ( $V_{DS} = 15\text{ Vdc}$ , $I_D = 5.0\text{ Adc}$ )	$g_{FS}$	-	10	-	Mhos

**DYNAMIC CHARACTERISTICS**

Input Capacitance	$(V_{DS} = 24\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{iss}$	-	680	950	pF
Output Capacitance		$C_{oss}$	-	210	300	
Reverse Transfer Capacitance		$C_{rss}$	-	70	135	

**SWITCHING CHARACTERISTICS** (Notes 7 & 8)

Turn-On Delay Time	$(V_{DD} = 15\text{ Vdc}$ , $I_D = 1\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_G = 6\ \Omega$ )	$t_{d(on)}$	-	9	18	ns
Rise Time		$t_r$	-	22	40	
Turn-Off Delay Time		$t_{d(off)}$	-	45	80	
Fall Time		$t_f$	-	45	80	
Turn-On Delay Time	$(V_{DD} = 15\text{ Vdc}$ , $I_D = 1\text{ A}$ , $V_{GS} = 4.5\text{ V}$ , $R_G = 6\ \Omega$ )	$t_{d(on)}$	-	13	30	ns
Rise Time		$t_r$	-	27	50	
Turn-Off Delay Time		$t_{d(off)}$	-	22	40	
Fall Time		$t_f$	-	34	70	
Gate Charge	$(V_{DS} = 15\text{ Vdc}$ , $V_{GS} = 10\text{ Vdc}$ , $I_D = 5\text{ A}$ )	$Q_T$	-	19	30	nC
		$Q_1$	-	2.4	-	
		$Q_2$	-	5.0	-	
		$Q_3$	-	4.3	-	

**BODY-DRAIN DIODE RATINGS** (Note 7)

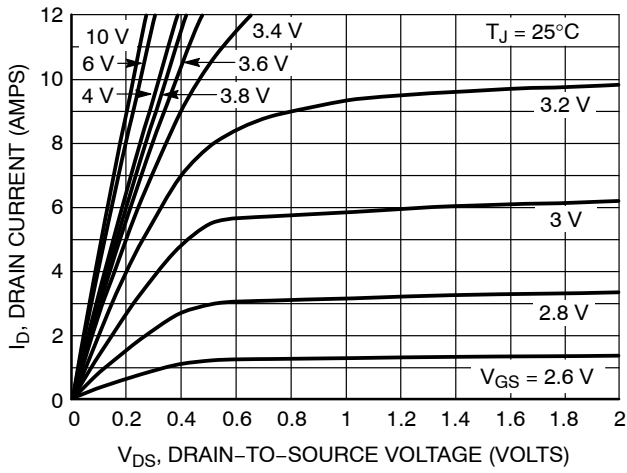
Diode Forward On-Voltage ( $I_S = 1.7\text{ Adc}$ , $V_{GS} = 0\text{ V}$ ) ( $I_S = 1.7\text{ Adc}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150^\circ\text{C}$ )	$V_{SD}$	- -	0.75 0.62	1.0 -	Vdc
Reverse Recovery Time ( $I_S = 5\text{ A}$ , $V_{GS} = 0\text{ V}$ , $dI_S/dt = 100\text{ A}/\mu\text{s}$ )	$t_{rr}$	-	26	-	ns
	$t_a$	-	11	-	
	$t_b$	-	15	-	
Reverse Recovery Stored Charge ( $I_S = 5\text{ A}$ , $dI_S/dt = 100\text{ A}/\mu\text{s}$ , $V_{GS} = 0\text{ V}$ )	$Q_{RR}$	-	0.015	-	$\mu\text{C}$

7. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

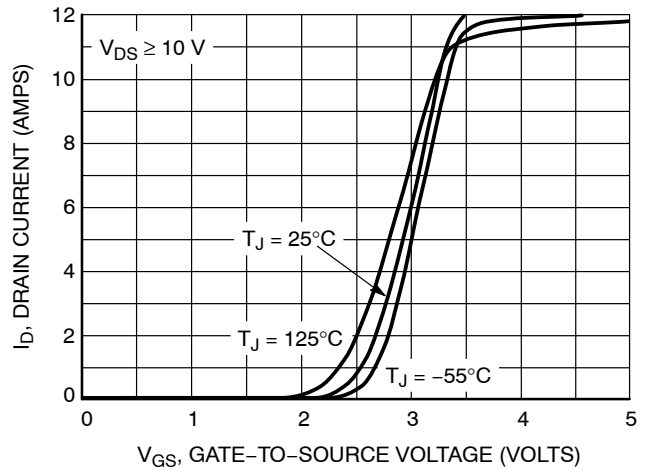
8. Switching characteristics are independent of operating junction temperature.

**NTMSD6N303, NVMSD6N303**

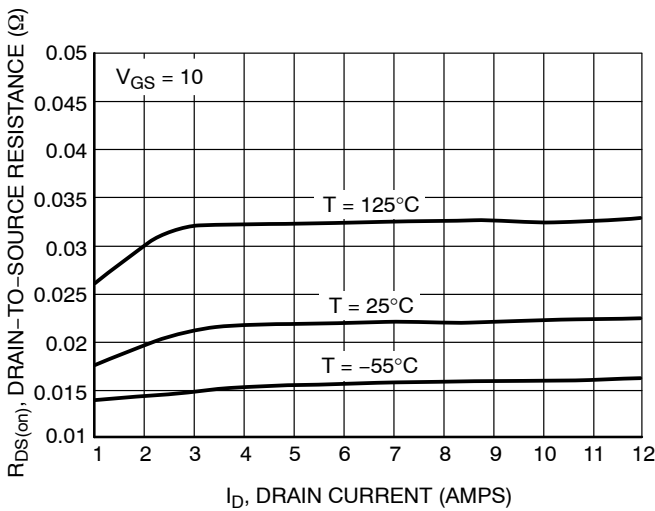
**TYPICAL MOSFET ELECTRICAL CHARACTERISTICS**



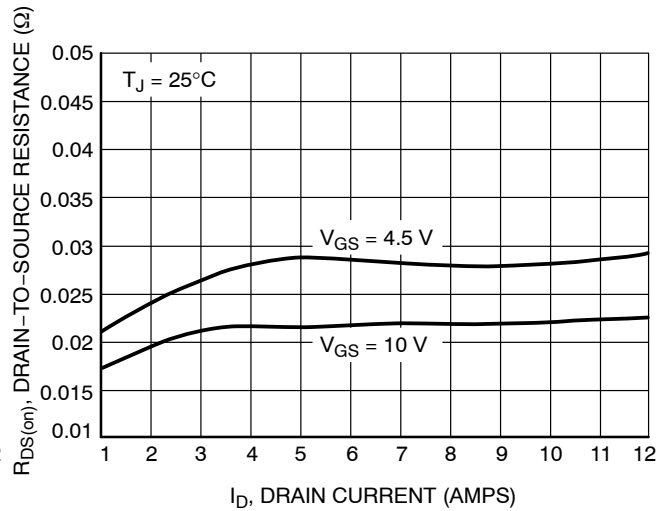
**Figure 1. On-Region Characteristics**



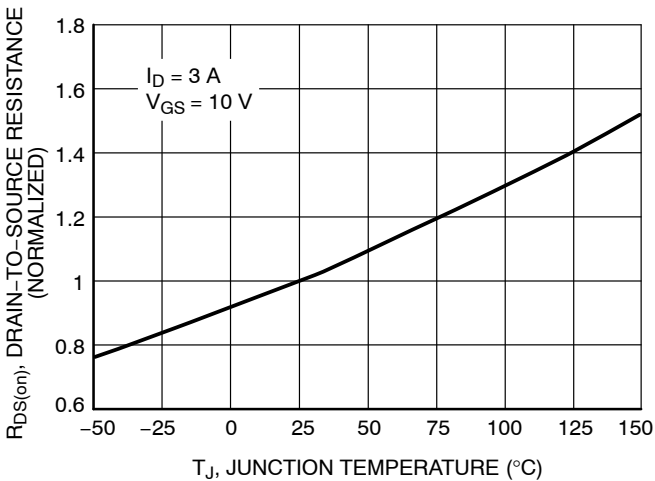
**Figure 2. Transfer Characteristics**



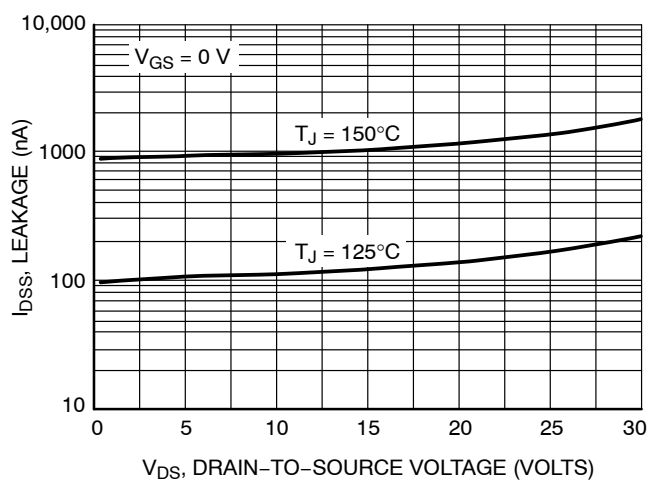
**Figure 3. On-Resistance versus Drain Current and Temperature**



**Figure 4. On-Resistance versus Drain Current and Gate Voltage**

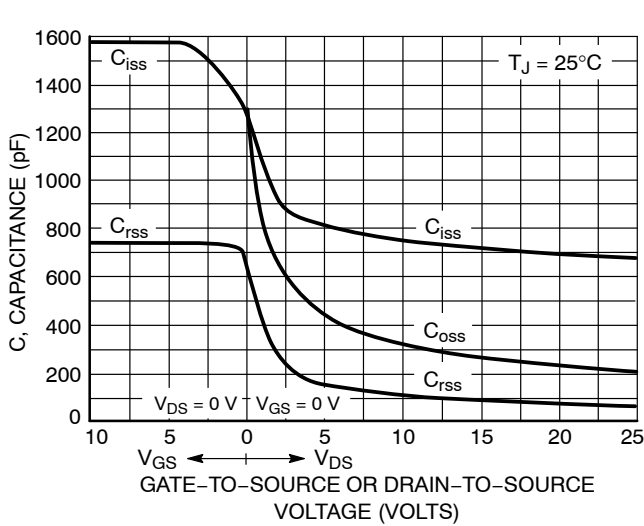


**Figure 5. On-Resistance Variation with Temperature**

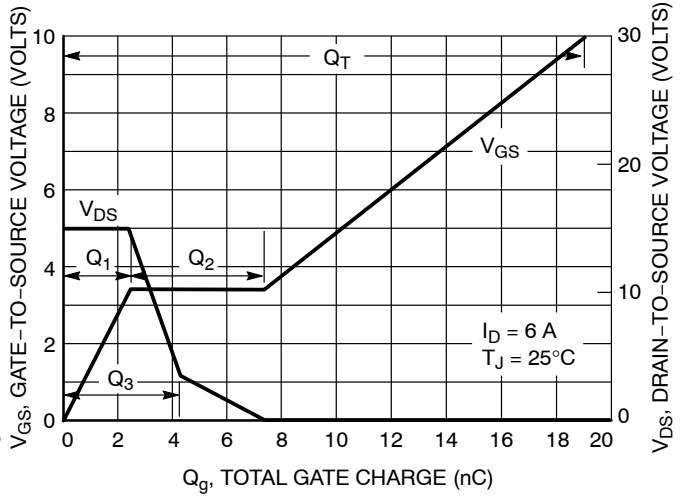


**Figure 6. Drain-to-Source Leakage Current versus Voltage**

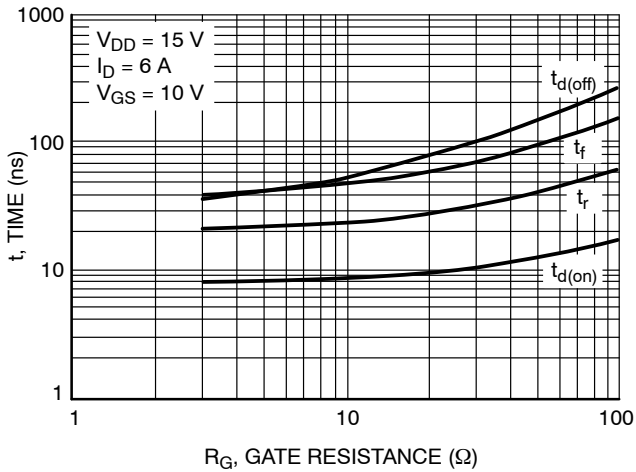
**NTMSD6N303, NVMSD6N303**



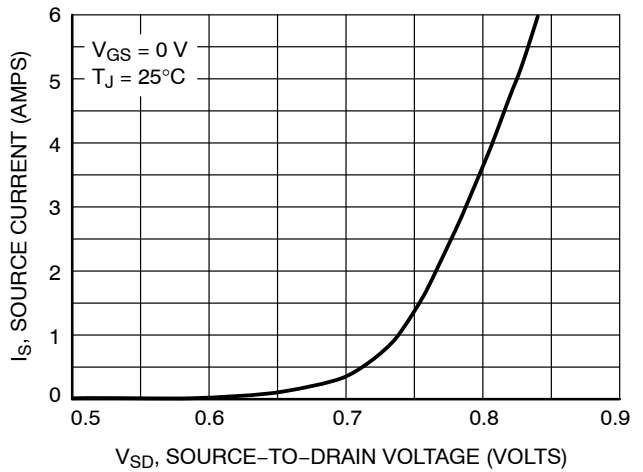
**Figure 7. Capacitance Variation**



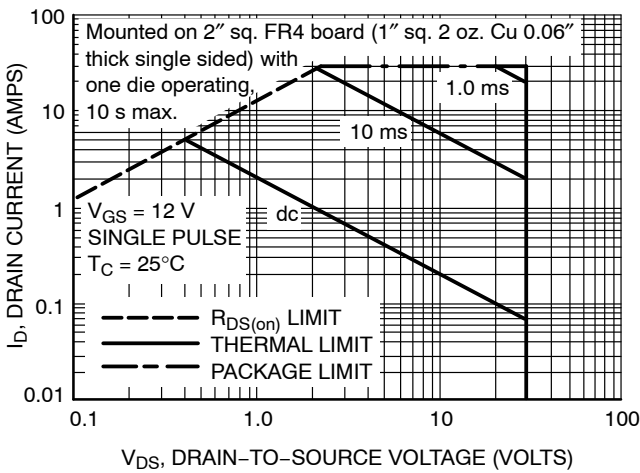
**Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge**



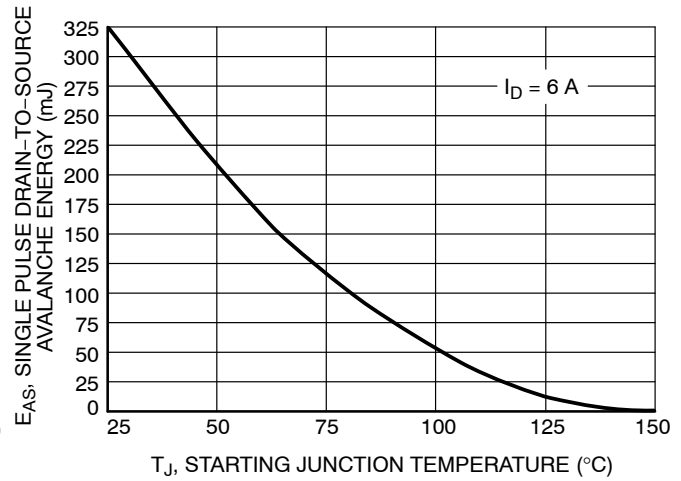
**Figure 9. Resistive Switching Time Variation versus Gate Resistance**



**Figure 10. Diode Forward Voltage versus Current**



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**



**Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature**

### NTMSD6N303, NVMSD6N303

#### TYPICAL FET ELECTRICAL CHARACTERISTICS

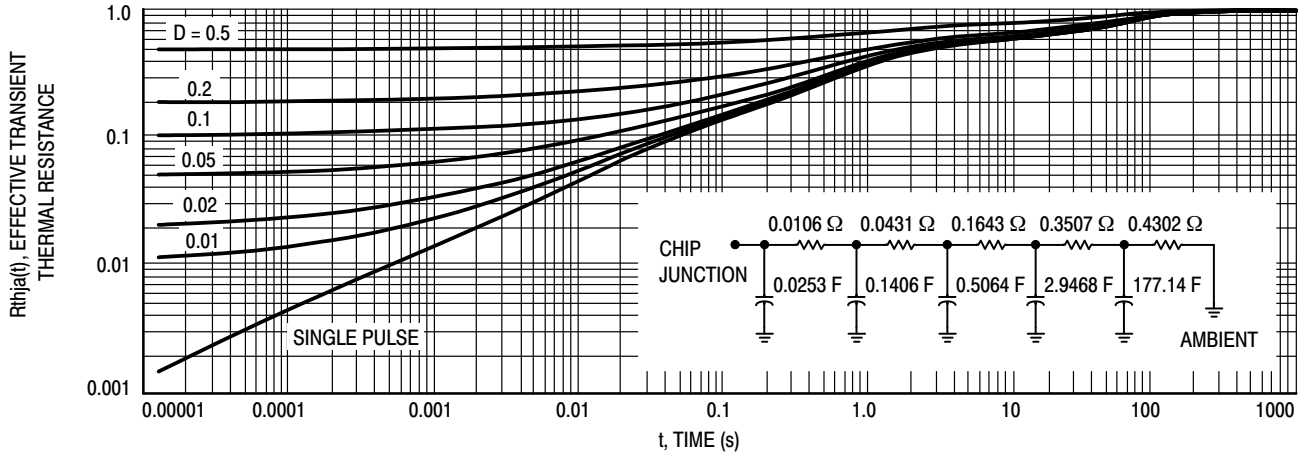


Figure 13. FET Thermal Response

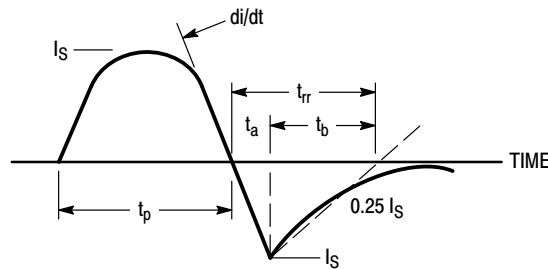


Figure 14. Diode Reverse Recovery Waveform

#### TYPICAL SCHOTTKY ELECTRICAL CHARACTERISTICS

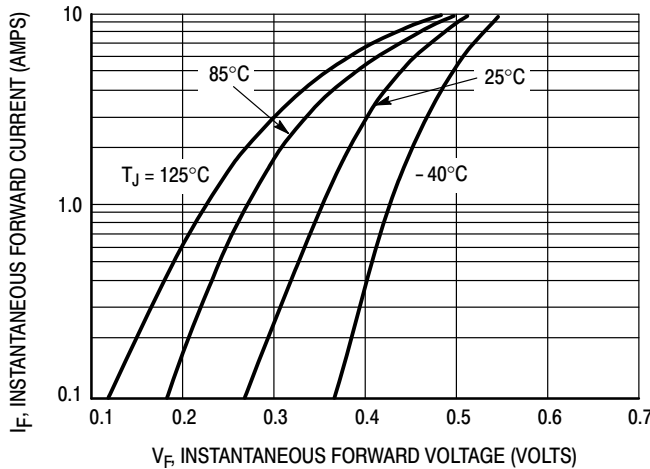


Figure 15. Typical Forward Voltage

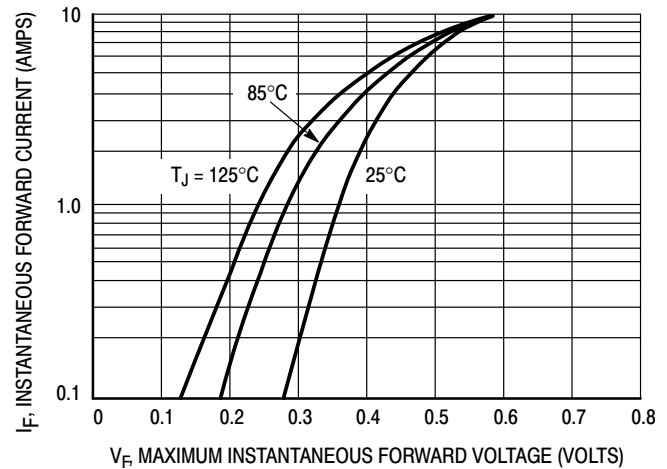
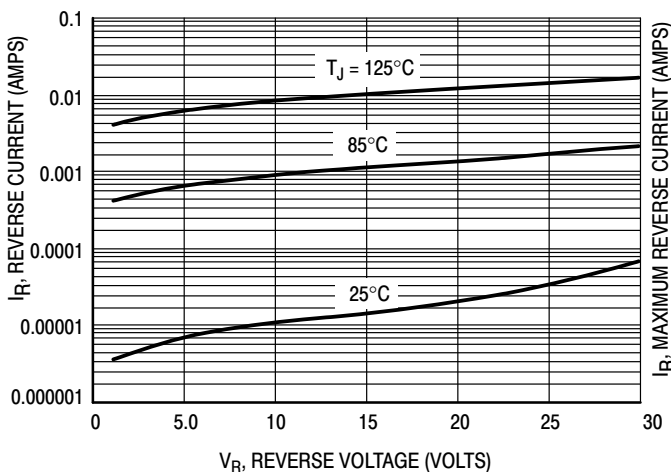


Figure 16. Maximum Forward Voltage

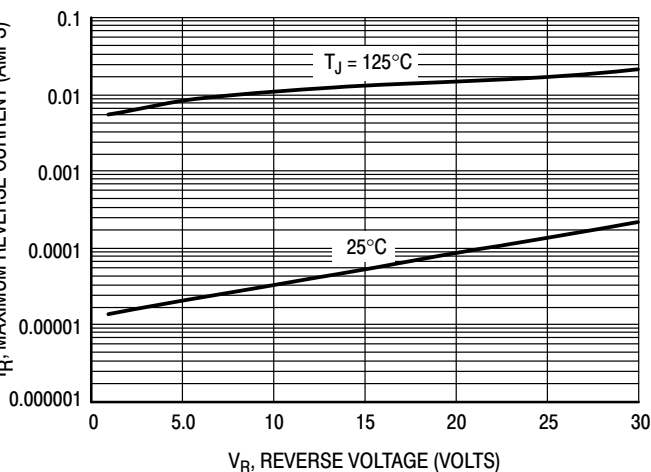


**NTMSD6N303, NVMSD6N303**

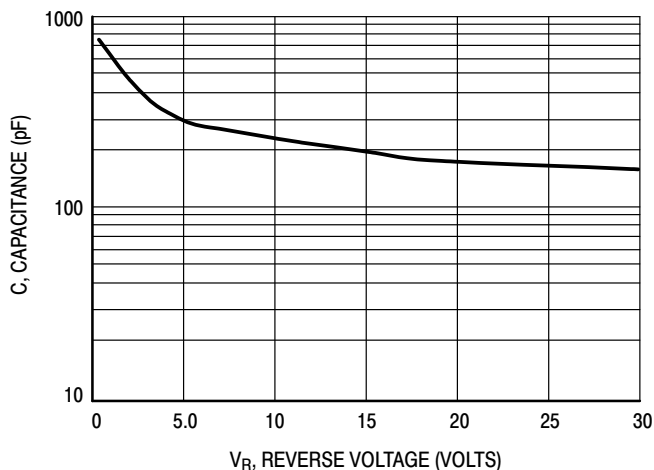
**TYPICAL SCHOTTKY ELECTRICAL CHARACTERISTICS**



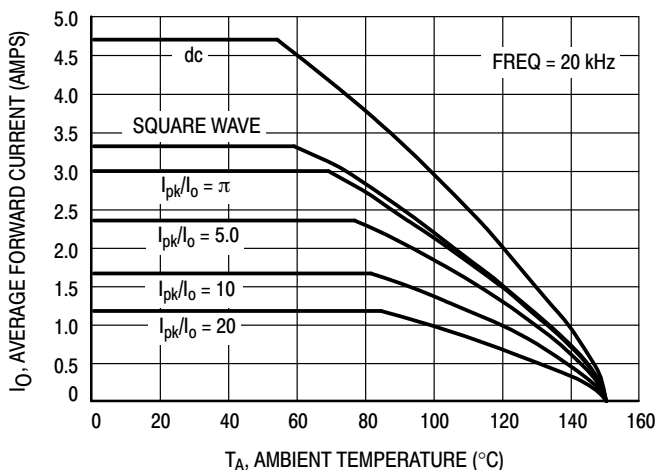
**Figure 17. Typical Reverse Current**



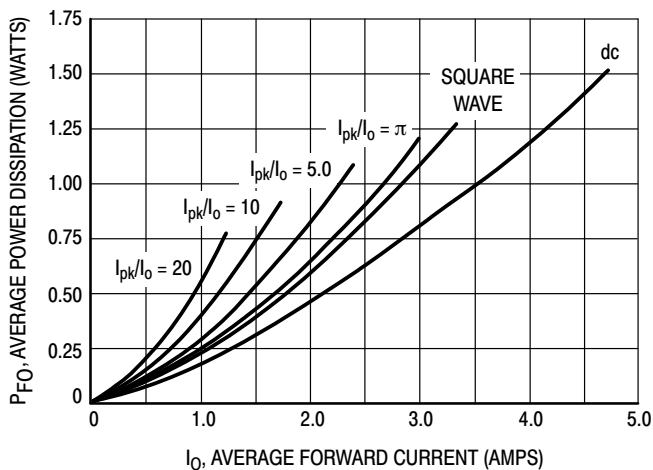
**Figure 18. Maximum Reverse Current**



**Figure 19. Typical Capacitance**



**Figure 20. Current Derating**



**Figure 21. Forward Power Dissipation**

**NTMSD6N303, NVMSD6N303**

**TYPICAL SCHOTTKY ELECTRICAL CHARACTERISTICS**

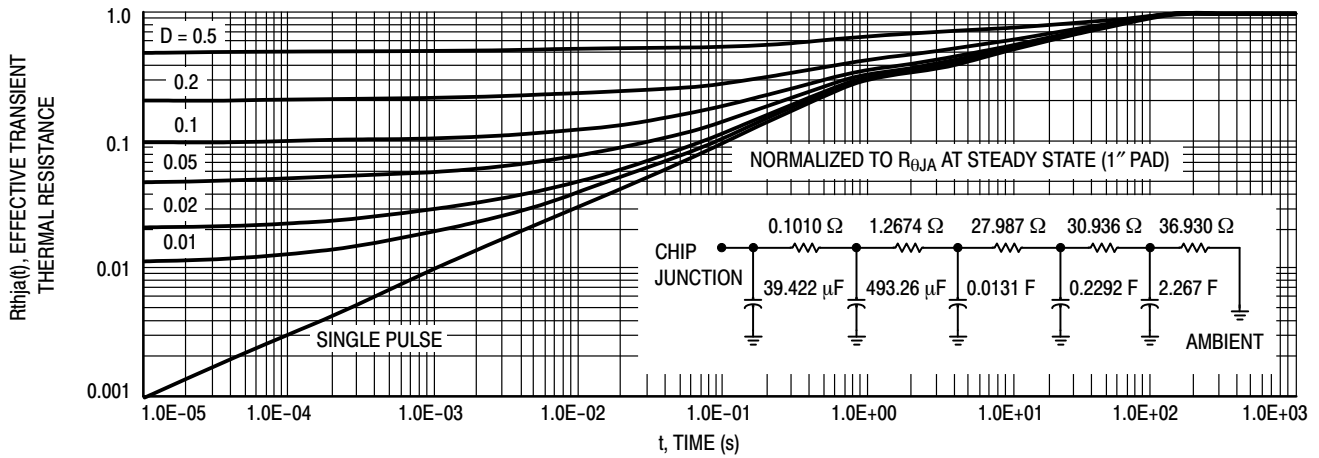
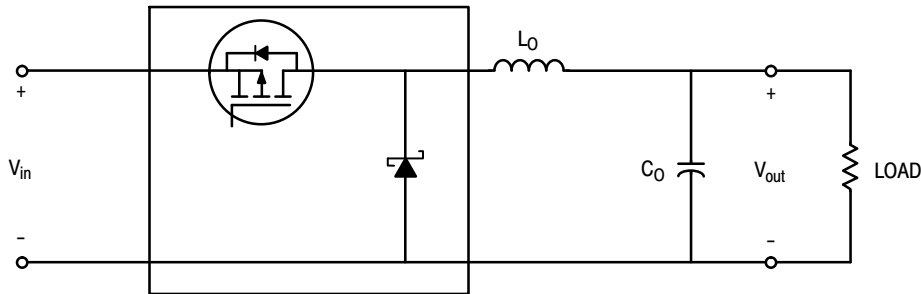


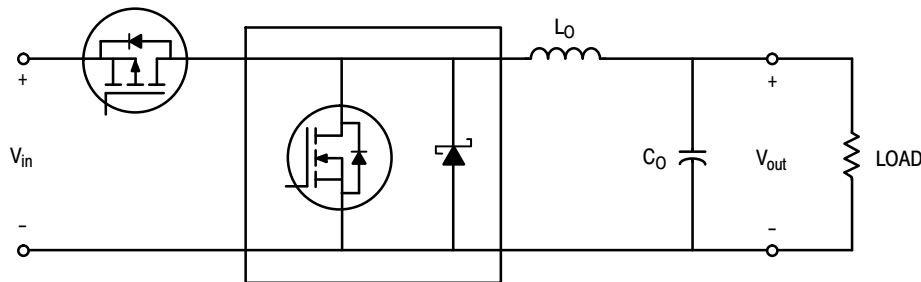
Figure 22. Schottky Thermal Response

**TYPICAL APPLICATIONS**

**STEP DOWN SWITCHING REGULATORS**



**Buck Regulator**

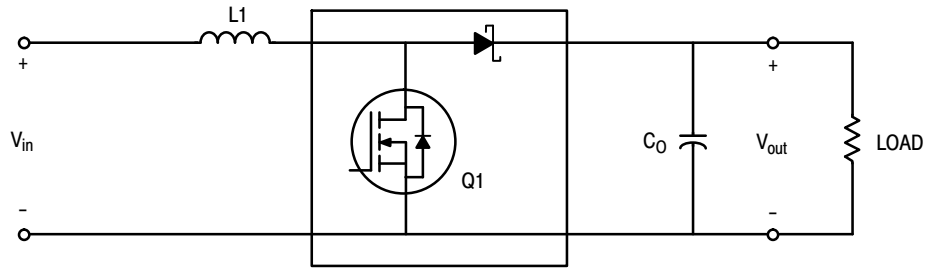


**Synchronous Buck Regulator**

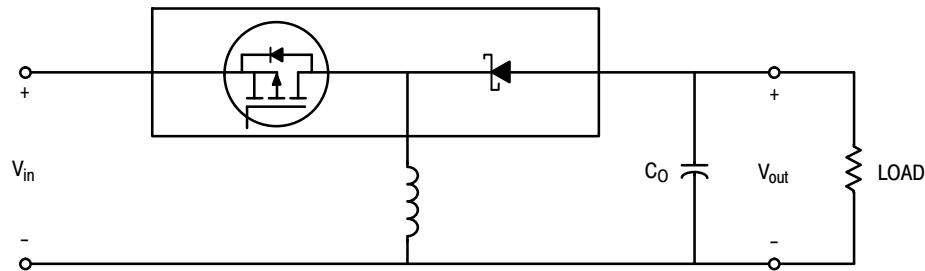
## NTMSD6N303, NVMSD6N303

### TYPICAL APPLICATIONS

#### STEP UP SWITCHING REGULATORS

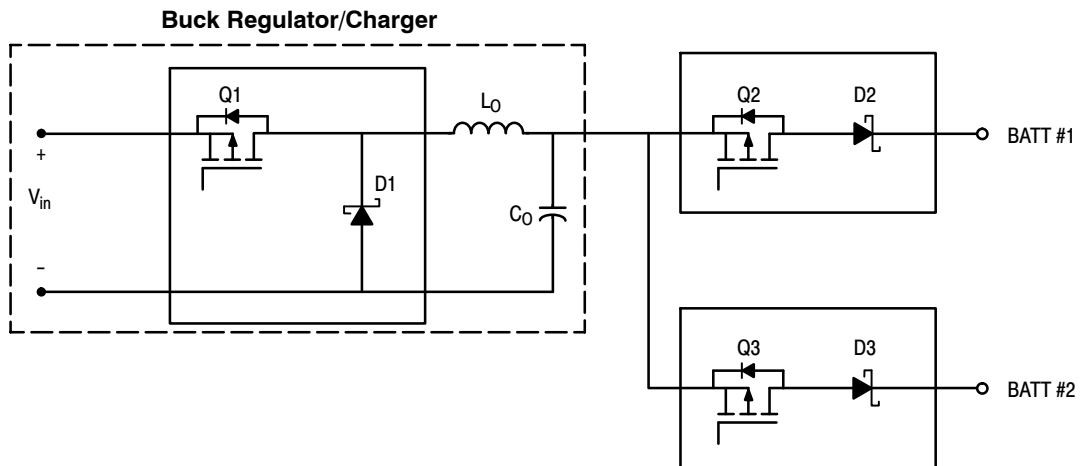


**Boost Regulator**



**Buck-Boost Regulator**

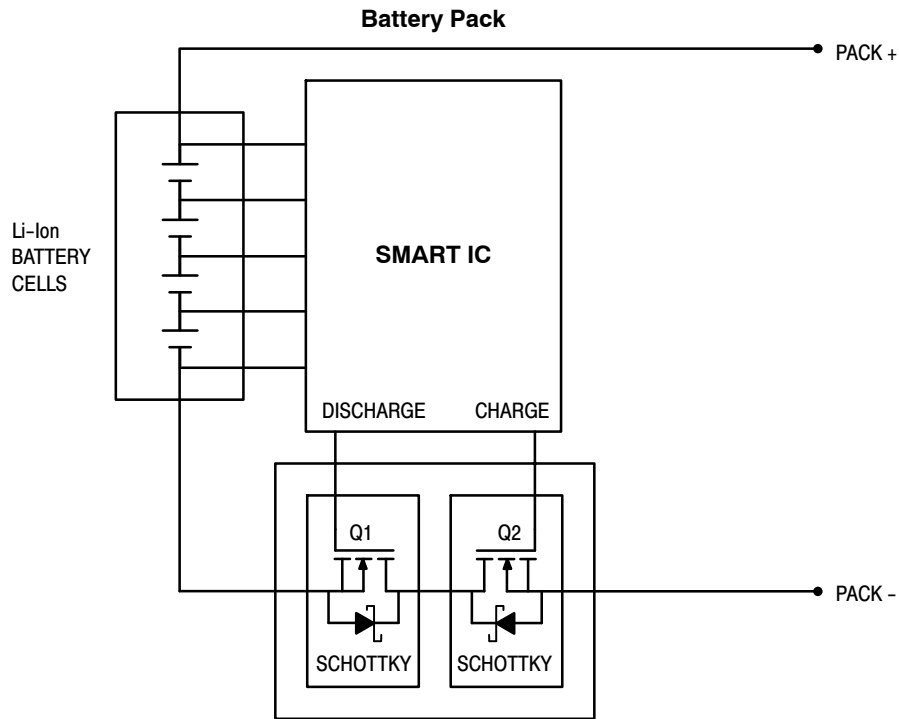
#### MULTIPLE BATTERY CHARGERS



## NTMSD6N303, NVMSD6N303

### TYPICAL APPLICATIONS

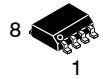
#### Li-Ion BATTERY PACK APPLICATIONS



- Applicable in battery packs which require a high current level.
- During charge cycle Q2 is on and Q1 is off. Schottky can reduce power loss during fast charge.
- During discharge Q1 is on and Q2 is off. Again, Schottky can reduce power dissipation.
- Under normal operation, both transistors are on.



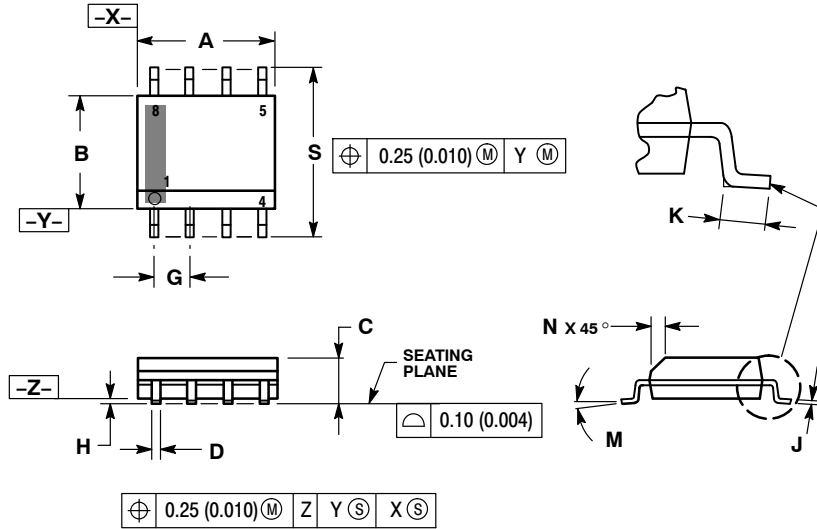
**MECHANICAL CASE OUTLINE  
PACKAGE DIMENSIONS**



SCALE 1:1

**SOIC-8 NB  
CASE 751-07  
ISSUE AK**

DATE 16 FEB 2011



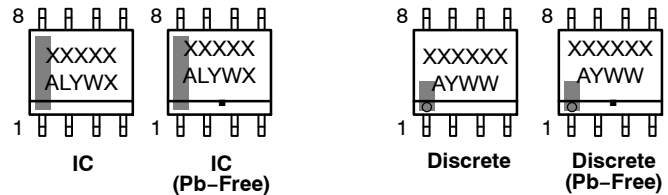
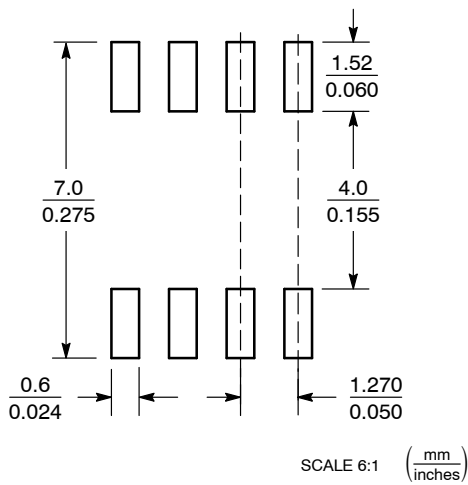
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

**GENERIC MARKING DIAGRAM\***

**SOLDERING FOOTPRINT\***



XXXXXX = Specific Device Code  
 A = Assembly Location  
 L = Wafer Lot  
 Y = Year  
 W = Work Week  
 ■ = Pb-Free Package

XXXXXX = Specific Device Code  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**STYLES ON PAGE 2**

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**SOIC-8 NB**  
**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

- STYLE 1:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. COLLECTOR  
 4. EMITTER  
 5. EMITTER  
 6. BASE  
 7. BASE  
 8. EMITTER
- STYLE 2:  
 PIN 1. COLLECTOR, DIE, #1  
 2. COLLECTOR, #1  
 3. COLLECTOR, #2  
 4. COLLECTOR, #2  
 5. BASE, #2  
 6. EMITTER, #2  
 7. BASE, #1  
 8. EMITTER, #1
- STYLE 3:  
 PIN 1. DRAIN, DIE #1  
 2. DRAIN, #1  
 3. DRAIN, #2  
 4. DRAIN, #2  
 5. GATE, #2  
 6. SOURCE, #2  
 7. GATE, #1  
 8. SOURCE, #1
- STYLE 4:  
 PIN 1. ANODE  
 2. ANODE  
 3. ANODE  
 4. ANODE  
 5. ANODE  
 6. ANODE  
 7. ANODE  
 8. COMMON CATHODE
- STYLE 5:  
 PIN 1. DRAIN  
 2. DRAIN  
 3. DRAIN  
 4. DRAIN  
 5. GATE  
 6. GATE  
 7. SOURCE  
 8. SOURCE
- STYLE 6:  
 PIN 1. SOURCE  
 2. DRAIN  
 3. DRAIN  
 4. SOURCE  
 5. SOURCE  
 6. GATE  
 7. GATE  
 8. SOURCE
- STYLE 7:  
 PIN 1. INPUT  
 2. EXTERNAL BYPASS  
 3. THIRD STAGE SOURCE  
 4. GROUND  
 5. DRAIN  
 6. GATE 3  
 7. SECOND STAGE Vd  
 8. FIRST STAGE Vd
- STYLE 8:  
 PIN 1. COLLECTOR, DIE #1  
 2. BASE, #1  
 3. BASE, #2  
 4. COLLECTOR, #2  
 5. COLLECTOR, #2  
 6. EMITTER, #2  
 7. EMITTER, #1  
 8. COLLECTOR, #1
- STYLE 9:  
 PIN 1. EMITTER, COMMON  
 2. COLLECTOR, DIE #1  
 3. COLLECTOR, DIE #2  
 4. EMITTER, COMMON  
 5. EMITTER, COMMON  
 6. BASE, DIE #2  
 7. BASE, DIE #1  
 8. EMITTER, COMMON
- STYLE 10:  
 PIN 1. GROUND  
 2. BIAS 1  
 3. OUTPUT  
 4. GROUND  
 5. GROUND  
 6. BIAS 2  
 7. INPUT  
 8. GROUND
- STYLE 11:  
 PIN 1. SOURCE 1  
 2. GATE 1  
 3. SOURCE 2  
 4. GATE 2  
 5. DRAIN 2  
 6. DRAIN 2  
 7. DRAIN 1  
 8. DRAIN 1
- STYLE 12:  
 PIN 1. SOURCE  
 2. SOURCE  
 3. SOURCE  
 4. GATE  
 5. DRAIN  
 6. DRAIN  
 7. DRAIN  
 8. DRAIN
- STYLE 13:  
 PIN 1. N.C.  
 2. SOURCE  
 3. SOURCE  
 4. GATE  
 5. DRAIN  
 6. DRAIN  
 7. DRAIN  
 8. DRAIN
- STYLE 14:  
 PIN 1. N-SOURCE  
 2. N-GATE  
 3. P-SOURCE  
 4. P-GATE  
 5. P-DRAIN  
 6. P-DRAIN  
 7. N-DRAIN  
 8. N-DRAIN
- STYLE 15:  
 PIN 1. ANODE 1  
 2. ANODE 1  
 3. ANODE 1  
 4. ANODE 1  
 5. CATHODE, COMMON  
 6. CATHODE, COMMON  
 7. CATHODE, COMMON  
 8. CATHODE, COMMON
- STYLE 16:  
 PIN 1. EMITTER, DIE #1  
 2. BASE, DIE #1  
 3. EMITTER, DIE #2  
 4. BASE, DIE #2  
 5. COLLECTOR, DIE #2  
 6. COLLECTOR, DIE #2  
 7. COLLECTOR, DIE #1  
 8. COLLECTOR, DIE #1
- STYLE 17:  
 PIN 1. VCC  
 2. V2OUT  
 3. V1OUT  
 4. TXE  
 5. RXE  
 6. VEE  
 7. GND  
 8. ACC
- STYLE 18:  
 PIN 1. ANODE  
 2. ANODE  
 3. SOURCE  
 4. GATE  
 5. DRAIN  
 6. DRAIN  
 7. CATHODE  
 8. CATHODE
- STYLE 19:  
 PIN 1. SOURCE 1  
 2. GATE 1  
 3. SOURCE 2  
 4. GATE 2  
 5. DRAIN 2  
 6. MIRROR 2  
 7. DRAIN 1  
 8. MIRROR 1
- STYLE 20:  
 PIN 1. SOURCE (N)  
 2. GATE (N)  
 3. SOURCE (P)  
 4. GATE (P)  
 5. DRAIN  
 6. DRAIN  
 7. DRAIN  
 8. DRAIN
- STYLE 21:  
 PIN 1. CATHODE 1  
 2. CATHODE 2  
 3. CATHODE 3  
 4. CATHODE 4  
 5. CATHODE 5  
 6. COMMON ANODE  
 7. COMMON ANODE  
 8. CATHODE 6
- STYLE 22:  
 PIN 1. I/O LINE 1  
 2. COMMON CATHODE/VCC  
 3. COMMON CATHODE/VCC  
 4. I/O LINE 3  
 5. COMMON ANODE/GND  
 6. I/O LINE 4  
 7. I/O LINE 5  
 8. COMMON ANODE/GND
- STYLE 23:  
 PIN 1. LINE 1 IN  
 2. COMMON ANODE/GND  
 3. COMMON ANODE/GND  
 4. LINE 2 IN  
 5. LINE 2 OUT  
 6. COMMON ANODE/GND  
 7. COMMON ANODE/GND  
 8. LINE 1 OUT
- STYLE 24:  
 PIN 1. BASE  
 2. EMITTER  
 3. COLLECTOR/ANODE  
 4. COLLECTOR/ANODE  
 5. CATHODE  
 6. CATHODE  
 7. COLLECTOR/ANODE  
 8. COLLECTOR/ANODE
- STYLE 25:  
 PIN 1. VIN  
 2. N/C  
 3. REXT  
 4. GND  
 5. IOUT  
 6. IOUT  
 7. IOUT  
 8. IOUT
- STYLE 26:  
 PIN 1. GND  
 2. dv/dt  
 3. ENABLE  
 4. ILIMIT  
 5. SOURCE  
 6. SOURCE  
 7. SOURCE  
 8. VCC
- STYLE 27:  
 PIN 1. ILIMIT  
 2. OVLO  
 3. UVLO  
 4. INPUT+  
 5. SOURCE  
 6. SOURCE  
 7. SOURCE  
 8. DRAIN
- STYLE 28:  
 PIN 1. SW\_TO\_GND  
 2. DASIC OFF  
 3. DASIC\_SW\_DET  
 4. GND  
 5. V\_MON  
 6. VBULK  
 7. VBULK  
 8. VIN
- STYLE 29:  
 PIN 1. BASE, DIE #1  
 2. EMITTER, #1  
 3. BASE, #2  
 4. EMITTER, #2  
 5. COLLECTOR, #2  
 6. COLLECTOR, #2  
 7. COLLECTOR, #1  
 8. COLLECTOR, #1
- STYLE 30:  
 PIN 1. DRAIN 1  
 2. DRAIN 1  
 3. GATE 2  
 4. SOURCE 2  
 5. SOURCE 1/DRAIN 2  
 6. SOURCE 1/DRAIN 2  
 7. SOURCE 1/DRAIN 2  
 8. GATE 1

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